

NPN SILICON POWER TRANSISTORS

...designed for use in TV horizontal deflection output applications

FEATURES:

- * Low Collector-Emitter Saturation Voltage $V_{CE(sat)}$ = 1.0V(Max) @I_C=4.0A,I_B=0.4A * DC Current Gain
- * DC Current Gain hFE= 30-150@I_c= 1.0A
- * Larg Collector Current Capability

NPN 2SC2233

4.0 AMPERE SILICON POWER TRANASISTORS 60 VOLTS 40 WATTS

MAXIMUM RATINGS

Characteristic	Symbol	2SC2233	Unit
Collector-Emitter Voltage	V _{CEO}	60	V
Collector-Base Voltage	V _{CBO}	V _{CBO} 200	
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current - Continuous - Peak	I _C	4.0 10	Α
Base current	I _B	2.0	Α
Total Power Dissipation @T _C = 25°C Derate above 25°C	P _D	40 0.32	W/°C
Operating and Storage Junction Temperature Range	T _J ,T _{STG}	-55 to +150	°C

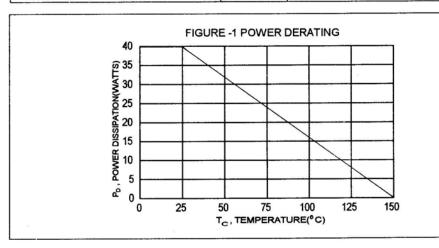
TO-220

PIN 1.BASE 2.COLLECTOR 3.EMITTER 4.COLLECTOR(CASE)

DIM	MILLIMETERS			
	MIN	MAX		
Α	14.68	16.00		
В	9.78	10.42		
С	5.02	6.60		
D	13.00	14.62		
E	3.10	4.19		
F	2.41	2.67		
G	1.10	1.67		
Н	0.69	1.01		
I	3.21	4.98		
J	1.14	1.40		
K	2.20	3.30		
L	0.28	0.61		
М	2.48	3.00		
0	3.50	4.00		

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	Rθjc	3.125	°C/W



MHz

ELECTRICAL CHARACTERISTICS ($T_c = 25^{\circ}C$ unless otherwise noted)

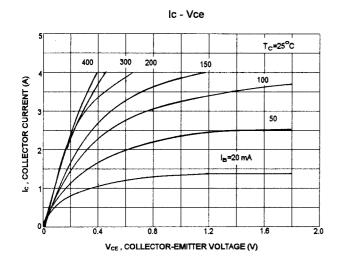
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			_	
Collector-Emitter Voltage (I _C = 50 mA, I _B = 0)	V _{CEO}	60		V
Emitter-Base Voltage (I _B = 1.0 mA, I _C = 0)	V _{EBO}	5.0		V
Collector Cutoff Current (V _{CB} = 170 V, I _E = 0)	Ісво		10	uA
Emitter Cutoff Current (V _{EB} = 5.0 V, I _C = 0)	I _{EBO}		10	uA
ON CHARACTERISTICS (1)				
DC Current Gain (I _C = 1.0 A,V _{CE} = 5.0 V) (I _C = 4.0 A,V _{CE} = 5.0 V)	hFE	30 20	150	
Collector-Emitter Saturation Voltage (I _C = 4.0 A, I _B = 400 mA)	V _{CE(sat)}		1.0	V
Base-Emitter Saturation Voltage (I _C = 4.0 A, I _B = 400 mA)	V _{BE(sat)}		1.5	V

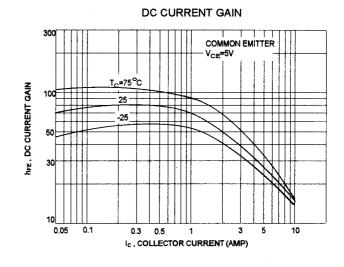
f_T

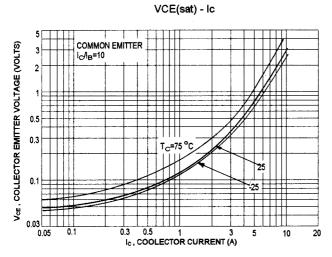
5.0

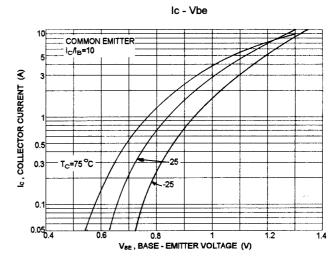
Current-Gain-Bandwidth Product (I_C = 0.5 A, V_{CE} = 5.0 V, f = 1.0 MHz) (1) Pulse Test: Pulse Width =300 μs, Duty Cycle ≦ 2.0%

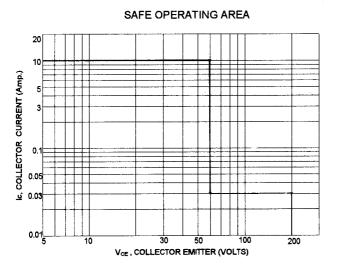
DYNAMIC CHARACTERISTICS

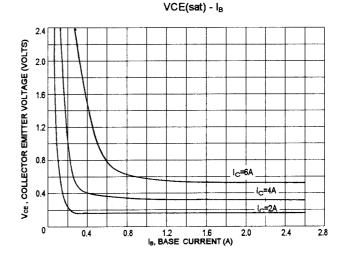














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